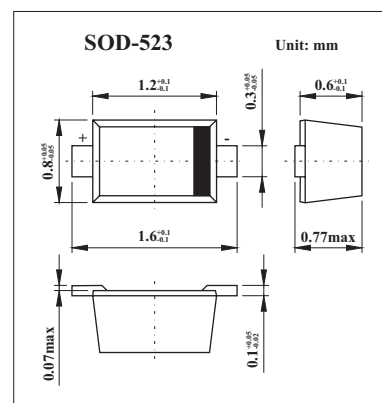


Schottky barrier diode

1PS79SB30

■ Features

- Very Low forward voltage
- Very Low reverse current
- Guard ring protected
- Ultra small plastic SMD package.

■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Conditions	Min	Max	Unit
continuous reverse voltage	V_R			40	V
continuous forward current	I_F			200	mA
repetitive peak forward current	I_{FSM}	$t_p \leq 1 \text{ s}; \delta \leq 0.5$		300	mA
non-repetitive peak forward current	I_{FSM}	$t = 8.3 \text{ ms}$ half sinewave; JEDEC method		1	A
storage temperature	T_{stg}		-65	+150	$^\circ\text{C}$
junction temperature	T_j			150	$^\circ\text{C}$
operating ambient temperature	T_{amb}		-65	+150	$^\circ\text{C}$

■ Electrical Characteristics $T_a = 25^\circ\text{C}$

Parameter	Symbol	Conditions	Typ	Max	Unit
forward voltage	V_F	$I_F = 0.1 \text{ mA}$	190	220	mV
		$I_F = 1 \text{ mA}$	250	290	
		$I_F = 10 \text{ mA}$	320	360	
		$I_F = 100 \text{ mA}$	440	500	
		$I_F = 200 \text{ mA}$	520	600	
capacitance reverse current	I_R	$V_R = 25 \text{ V}$, note 1;		0.5	μA
diode capacitance	C_d	$V_R = 1 \text{ V}$, $f = 1 \text{ MHz}$;		20	pF
thermal resistance from junction to ambient	$R_{th j-a}$			450	K/W

Note

1. Pulse test: pulse width = $300 \mu\text{s}$, $\delta = 0.02$.

■ Marking

Marking	G1
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